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(71) Applicant: **APPLIED MATERIALS, INC.** [US/US];
3050 Bowers Avenue, Santa Clara, California 95054 (US).

(72) Inventors: **GANGULI, Seshadri**; 3050 Bowers Avenue,
Santa Clara, California 95054 (US). **WRENCH, Jacqueline S.**; 3473 N 1st St, Apt 218, San Jose, California
95134 (US). **YANG, Yixiong**; 3050 Bowers Avenue, San-

ta Clara, California 95054 (US). **YANG, Yong**; No. 531
Qianwangchao Village, Tengzhou City, Shandong 277518
(CN). **GANDIKOTA, Srinivas**; 3050 Bowers Avenue,
Santa Clara, California 95054 (US).

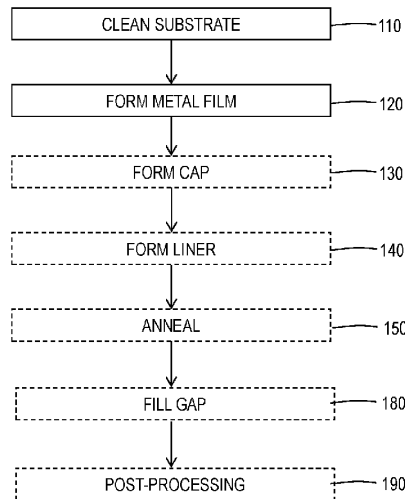
(74) Agent: **SMIRK, Rebecca A.**; Servilla Whitney LLC, 33
Wood Avenue South, Suite 830, Iselin, New Jersey 08830
(US).

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(54) Title: METHODS OF FORMING MOLYBDENUM CONTACTS

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FIG. 1A



(57) Abstract: Methods for forming a semiconductor structure are described. The method includes cleaning a substrate to form a substrate surface substantially free of oxide, exposing the substrate surface to a first molybdenum precursor, and exposing the substrate surface to a reactant to selectively deposit a first molybdenum film on the substrate surface. The method may be performed in a processing chamber without breaking vacuum. The method may also include forming one or more of a cap layer and a liner and annealing the substrate. The method may also include depositing a second molybdenum film on the substrate surface.

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